



#39/Amendment
10-25-02
JND
PATENT

1987

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of)	Group Art Unit: 2812
)	
Shunpei YAMAZAKI et al.)	Examiner: R. Booth
)	
Serial No. 09/255,777)	
)	
Filed: February 23, 1999)	
)	
For: SEMICONDUCTOR DEVICE)	Dated: October 18, 2002
AND METHOD FOR)	
FORMING THE SAME)	

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AMENDMENT

Commissioner for Patents
Washington, D. C. 20231

Sir:

In response to the Office Action mailed June 19, 2002, please amend the above identified application as follows:

IN THE CLAIMS:

Claims 12, 13, 16, 18, 19, 23, 24, 28, 29, 30, 32, 34, 37, 41, 53, 55, 58, 65, 66 and 68 are presented below in their amended form. The amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

12. (Amended) A method for fabricating a semiconductor device, comprising the steps

of:

forming a semiconductor film comprising amorphous silicon over an insulating surface;

forming an insulating film on said semiconductor film;

crystallizing at least a channel formation region of said semiconductor film by laser irradiation through said insulating film;